

长春新产业光电技术有限公司

Changchun New Industries Optoelectronics Tech, Co., Ltd.

DATA SHEET

DPS-532-E/1.5~4mJ

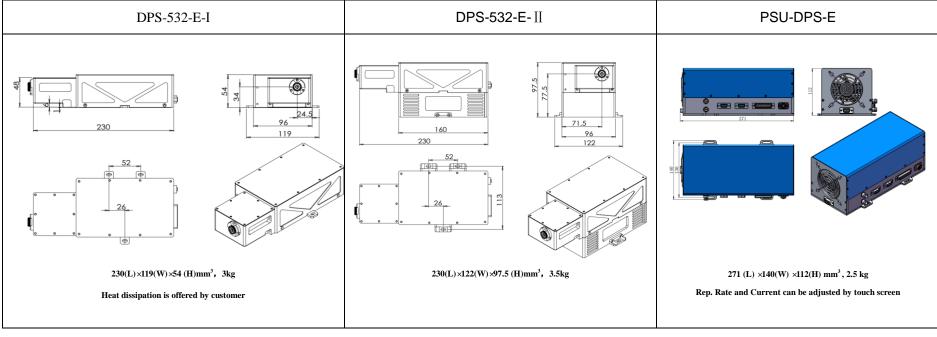
HIGH ENERGY DIODE PUMPED ALL-SOLID-STATE Q-SWITCHED LASER

High energy diode pumped all solid state Q-switched laser at 532nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in LIBS, LIF, ICP-MS, LCD repair, scientific research, and so on.



SPECIFICATIONS

Wavelength (nm)	532±1		
Operating mode	Q-switched: EO (Electro-optic)		
Single pulse energy (mJ)	1.5	4	
Pulse duration (ns)	<4		
Rep. rate (Hz)	1~50 (Optional), EXT		
Energy stability (rms)	<3%, <5%		一一 河下下
Beam divergence, full angle (mrad)	<3		
Beam diameter (mm)	~1		
Beam height from base plate (mm)	34	77.5	AVOID EXPOSURE: Laser radiation is emitted from this APERTURE
Warm-up time (minutes)	<15		DANGER
Cooled method	Conduction (DPS-532-E- I)	Air cooled (DPS-532-E-II)	INVISIBLE LASER RADIATION-AVOID DIRECT
Operating temperature (°C)	15~30		EXPOSURE TO BEAM Single Pulse Energy ≤150mJ Pulse Duration <20msec Wavelength 1000-1600mm
Power supply (24V DC)	PSU-DPS-E		CLASS IIIb LASER PRODUCT This device complex with 21 CTR1040.10 and 1040.11 Chemachen New Industries Ortwolectowics Tech. Co., Lul. (CNI)
Expected lifetime (pulses)	10 9		Changchen New Industries Ophotectowers Tech. Us., LM, (CM) No.388 Jinhu Road, High-tech Zore, Changchur, China
Warranty period	1 year		



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